## **Supporting information**

Solubility and crystallographic facet tailoring of (GaN)<sub>1-x</sub>(ZnO)<sub>x</sub> pseudobinary solid-solution nanostructures as promising photocatalysts

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**Figure S1** (a) EDS spectra of  $(GaN)_{1-x}(ZnO)_x$  nanorods synthesized at different temperature. (b) Comparative atomic percentages of Ga and Zn elements in the three typical samples with a nitridation time of 30, 60, 120 min, respectively (the data is obtained based on the EDS measurements in TEM and SEM modes).

**Figure S2** (a) XRD patterns of as-synthesized samples at 800 °C under different growth time: 0 (before nitridation), 30, 60 and 120 min; (b) magnified curves of (100) and (002) peaks for all samples;

*Figure S3* (a)UV-visible diffuse reflectance spectra of obtained samples before nitridation and after 30, 60 and 120 min nitridation at 800 °C; (b) UV-visible diffuse reflectance spectra of obtained samples under different growth temperatures (alternately 800, 850, 900 °C) for 60 min;

*Figure S4* (a) Sectional view images of three typical morphology nanorods at different growth time: 30, 60 and 120 min;



Figure S1.



Figure S2.



Figure S3.



Figure S4.